



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

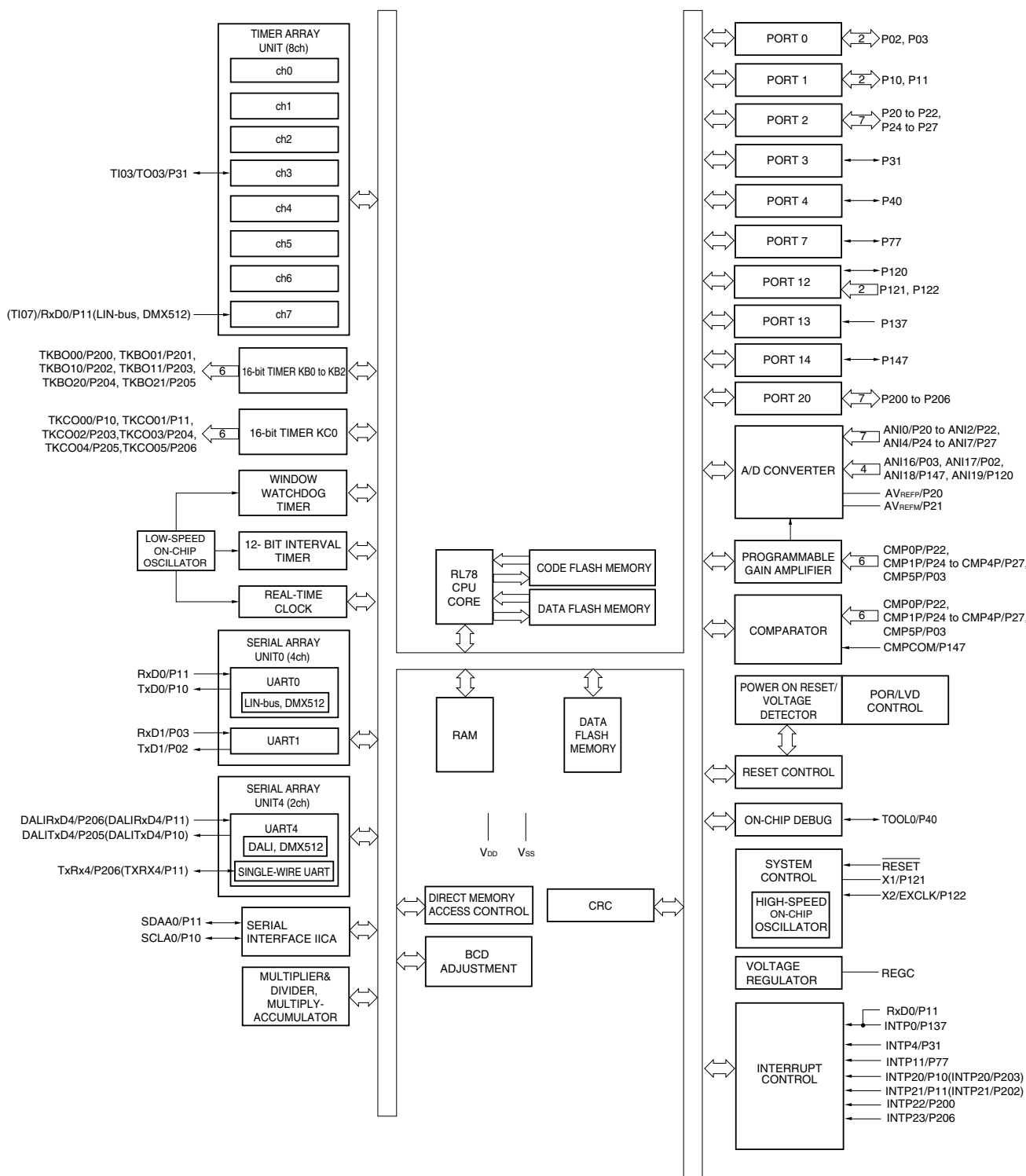
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	13
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1076cgsp-x0

1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1)** and **Figure 15-20 Format of Input Switch Control Register (ISC)** in the RL78/I1A User's Manual.

(3/3)

Item	20-pin	30-pin	38-pin
	R5F1076C	R5F107AC, R5F107AE	R5F107DE
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 V (TYP.) • Power-down-reset: 1.50 V (TYP.) 		
Voltage detector	<ul style="list-style-type: none"> • Rising edge: 2.81 V to 4.06 V (6 stages) • Falling edge: 2.75 V to 3.98 V (6 stages) 		
On-chip debug function	Provided		
Power supply voltage	$V_{DD} = 2.7$ to 5.5 V		
Operating ambient temperature	$T_A = -40$ to $+105^{\circ}\text{C}$ (G: Industrial applications), $T_A = -40$ to $+125^{\circ}\text{C}$ (M: Industrial applications)		

($T_A = -40$ to $+105^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	$0.8V_{DD}$		V_{DD}	V
	V_{IH2}	P03, P10, P11	TTL input buffer $4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.1		V_{DD}	V
			TTL input buffer $3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	2.0		V_{DD}	V
			TTL input buffer $2.7\text{ V} \leq V_{DD} < 3.3\text{ V}$	1.5		V_{DD}	V
Input voltage, low	V_{IL1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		$0.2V_{DD}$	V
	V_{IL2}	P03, P10, P11	TTL input buffer $4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	0		0.8	V
			TTL input buffer $3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	0		0.5	V
			TTL input buffer $2.7\text{ V} \leq V_{DD} < 3.3\text{ V}$	0		0.32	V

Caution The maximum value of V_{IH} of pins P02, P10 to P12 is V_{DD} , even in the N-ch open-drain mode.

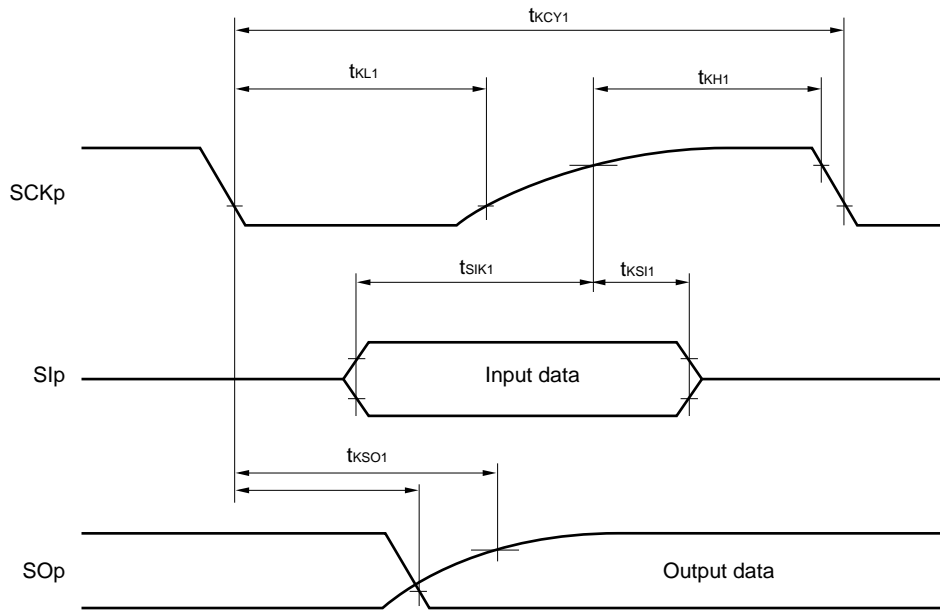
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.7 V ≤ VDD ≤ 5.5 V, VSS = 0 V) (2/2)

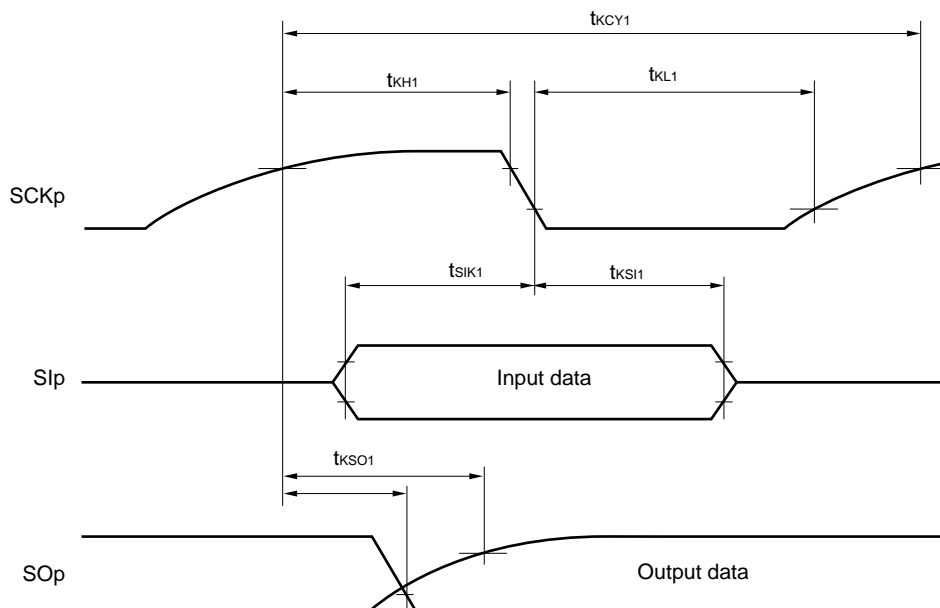
Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} ^{Note 2}	HALT mode	HS (high-speed main) mode ^{Note 7}	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA	
					V _{DD} = 3.0 V		0.72	2.9	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA	
					V _{DD} = 3.0 V		0.57	2.3	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA	
					V _{DD} = 3.0 V		0.50	1.7	mA	
				LS (low-speed main) mode ^{Note 7}	f _{IH} = 8 MHz ^{Note 4} , T _A = −40 to +85°C	V _{DD} = 3.0 V		320	910	μA
					HS (high-speed main) mode ^{Note 7}	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.40	1.9
				Resonator connection				0.50	2.0	mA
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V		Square wave input		0.40	1.9	mA
						Resonator connection		0.50	2.0	mA
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V		Square wave input		0.24	1.02	mA
			Resonator connection				0.30	1.08	mA	
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input			0.24	1.02	mA	
				Resonator connection			0.30	1.08	mA	
			LS (low-speed main) mode ^{Note 7}	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V, T _A = −40 to +85°C	Square wave input		130	720	μA	
					Resonator connection		170	760	μA	
			HS (high-speed main) mode ^{Note 7}	f _{IH} = 4 MHz ^{Note 4} f _{PLL} = 64 MHz, f _{CLK} = 32 MHz	V _{DD} = 5.0 V		1.15	4.0	mA	
					V _{DD} = 3.0 V		1.15	4.0	mA	
				f _{IH} = 4 MHz ^{Note 4} f _{PLL} = 64 MHz, f _{CLK} = 16 MHz	V _{DD} = 5.0 V		0.95	3.2	mA	
					V _{DD} = 3.0 V		0.95	3.2	mA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.70	μA	
					Resonator connection		0.47	0.89	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.33	0.70	μA	
					Resonator connection		0.52	0.89	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	1.90	μA	
					Resonator connection		0.60	2.09	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μA	
					Resonator connection		0.73	2.99	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.27	6.10	μA	
					Resonator connection		1.46	6.29	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		3.04	15.5	μA	
					Resonator connection		3.23	15.7	μA	
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.18	0.50	μA
			T _A = +25°C					0.23	0.50	μA
			T _A = +50°C					0.27	1.70	μA
			T _A = +70°C					0.44	2.60	μA
			T _A = +85°C					1.17	5.90	μA
			T _A = +105°C					2.94	15.3	μA

(Notes and Remarks are listed on the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(7) DALI/UART4 mode

 $(T_A = -40$ to $+105^{\circ}\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				$f_{MCK}/12$		$f_{MCK}/12$	bps
		Maximum transfer rate theoretical value HS: $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$ LS: $f_{CLK} = 8\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6		0.6	Mbps

Remark f_{MCK} : Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating conditions of LS (low-speed main) mode is $T_A = -40$ to $+85^{\circ}\text{C}$.

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.7\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}		1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI4 to ANI7	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625	39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2, ANI4 to ANI7	0		AV_{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)	V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (HS (high-speed main) mode)	V_{TMPS25} ^{Note 4}			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

($T_A = -40$ to $+105^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = $V_{BGR}^{\text{Note 3}}$, Reference voltage (–) = $AV_{REFM} = 0\text{ V}^{\text{Note 4}}$, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	t_{CONV}	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	8-bit resolution			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			± 2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			± 1.0	LSB
Analog input voltage	V_{AIN}		0		$V_{BGR}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS} , the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM} .

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

($T_A = -40$ to $+125^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, $\overline{\text{RESET}}$	Normal input buffer	$0.8V_{DD}$		V_{DD}	V
	V_{IH2}	P03, P10, P11	TTL input buffer $4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.1		V_{DD}	V
			TTL input buffer $3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	2.0		V_{DD}	V
			TTL input buffer $2.7\text{ V} \leq V_{DD} < 3.3\text{ V}$	1.5		V_{DD}	V
Input voltage, low	V_{IL1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, $\overline{\text{RESET}}$	Normal input buffer	0		$0.2V_{DD}$	V
	V_{IL2}	P03, P10, P11	TTL input buffer $4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	0		0.8	V
			TTL input buffer $3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	0		0.5	V
			TTL input buffer $2.7\text{ V} \leq V_{DD} < 3.3\text{ V}$	0		0.32	V

Caution The maximum value of V_{IH} of pins P02, P10 to P12 is V_{DD} , even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes**
1. Total current flowing into V_{DD} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }20\text{ MHz}$
 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

- Notes**
1. Current flowing to the V_{DD} .
 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2} , and I_{RTC} , when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.
 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and I_{FIL} operating current). The current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2} , and I_{IT} , when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.
 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} , and I_{WDT} , when the watchdog timer is operating.
 6. Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} , when the A/D converter is operating in operating mode or in HALT mode.
 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
 8. Current flowing during self-programming operation.
 9. Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} , and I_{PGA} , when the programmable gain amplifier is operating in operating mode or in HALT mode.
 10. Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} , and I_{CMP} , when the comparator is operating.
 11. This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 12. Current flowing only during data flash rewrite.
 13. See **21.3.3 SNOOZE mode in the RL78/I1A User's Manual** for shift time to the SNOOZE mode.

- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$
 5. Example of calculating current value when using programmable gain amplifier and comparator.
Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when $AV_{REFP} = V_{DD} = 5.0\text{ V}$)

$$\begin{aligned}
 & I_{CMP} \times 3 + I_{VREF} + I_{PGA} + I_{IREF} \\
 &= 41.4 [\mu\text{A}] \times 3 + 14.8 [\mu\text{A}] \times 1 + 210 [\mu\text{A}] + 3.2 [\mu\text{A}] \\
 &= 352.2 [\mu\text{A}]
 \end{aligned}$$

- Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when $AV_{REFP} = V_{DD} = 5.0\text{ V}$)

$$\begin{aligned}
 & I_{CMP} \times 2 + I_{IREF} \\
 &= 41.4 [\mu\text{A}] \times 2 + 3.2 [\mu\text{A}] \\
 &= 86.0 [\mu\text{A}]
 \end{aligned}$$

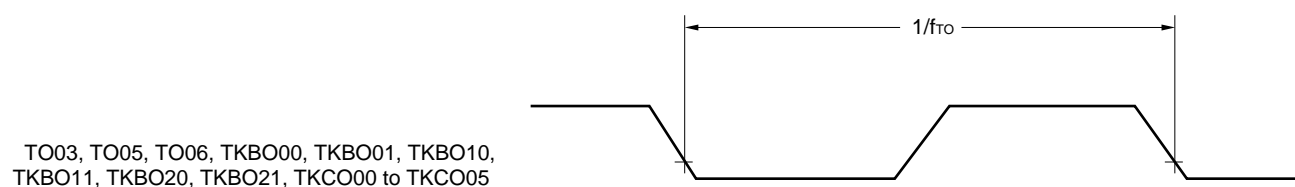
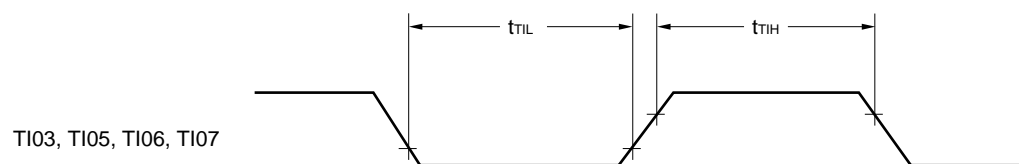
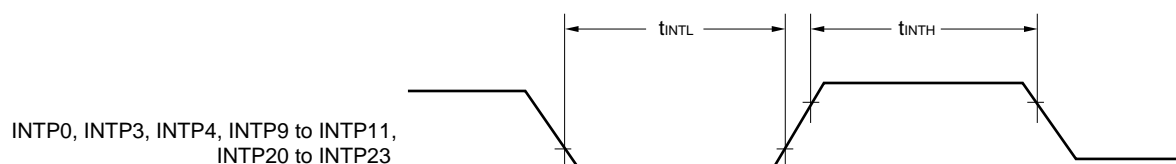
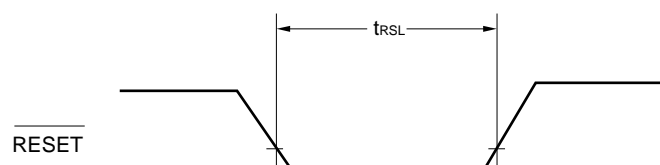
3.4 AC Characteristics

(T_A = -40 to $+125^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	0.05		1	μs
		Subsystem clock (f _{SUB}) operation		28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode T _A = -40 to $+105^\circ\text{C}$	0.05		1	μs
External system clock frequency	f _{EX}			1.0		20.0	MHz
	f _{EXS}			32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}			24			ns
	t _{EXHS} , t _{EXLS}			13.7			μs
TI03, TI05, TI06, TI07 input high-level width, low-level width	t _{TIH} , t _{TIL}			2/f _{MCK} +10			ns
TO03, TO05, TO06, TKBO00, TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)	f _{TO}	HS (high-speed main) mode	4.0 V ≤ V _{DD} ≤ 5.5 V			5	MHz
			2.7 V ≤ V _{DD} < 4.0 V			4	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23	2.7 V ≤ V _{DD} ≤ 5.5 V	1			μs
RESET low-level width	t _{RSL}			10			μs

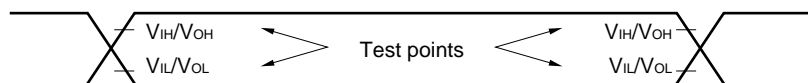
Remark f_{MCK}: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

TI/TO Timing**Interrupt Request Input Timing****RESET Input Timing**

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode)

($T_A = -40$ to $+125^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

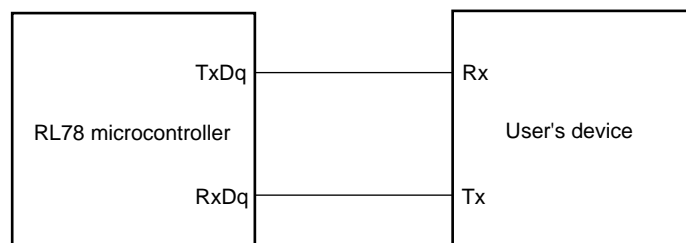
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate ^{Note 1}				$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note 2}		3.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

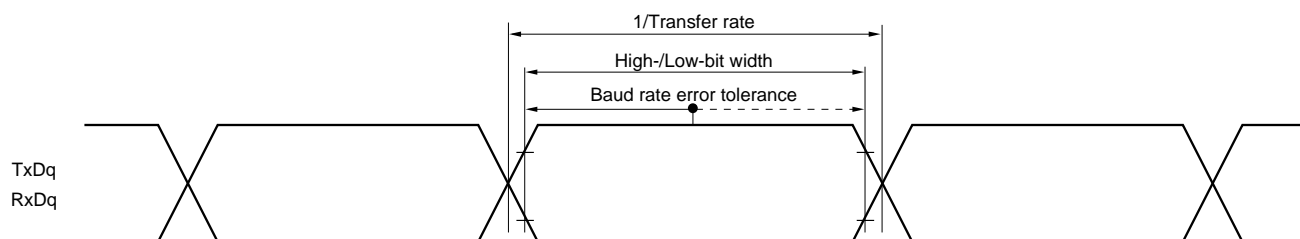
2. The operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 20 MHz ($2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$)

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)

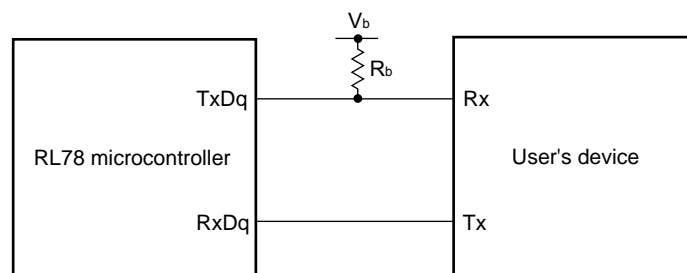
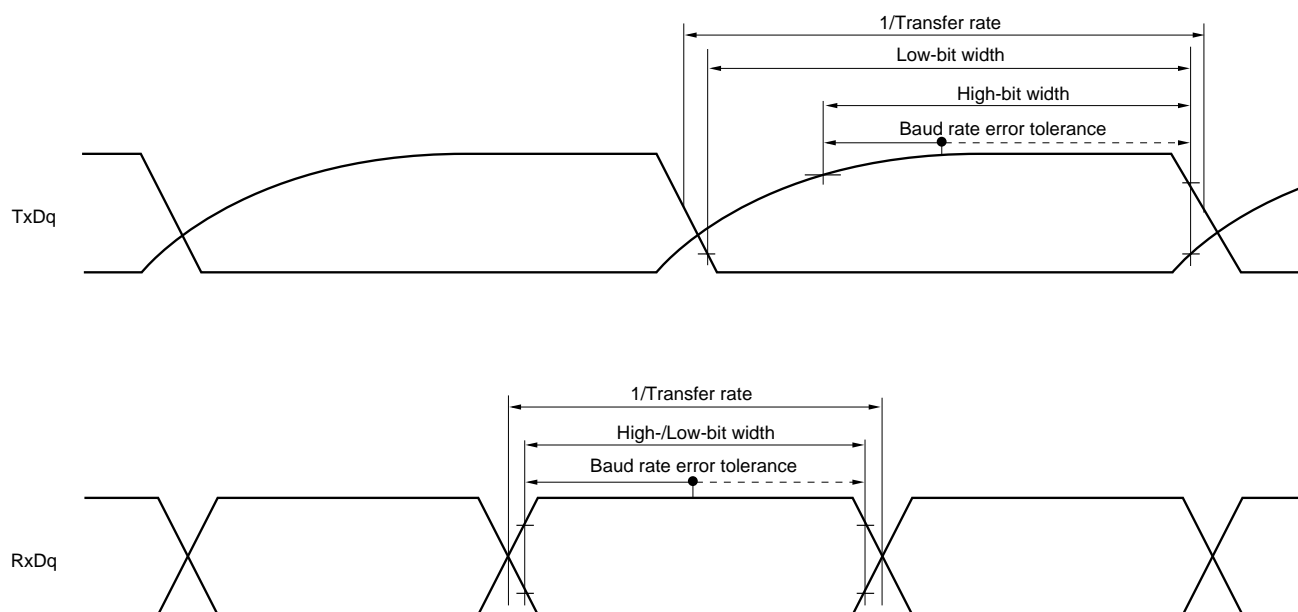


Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

UART mode connection diagram (during communication at different potential)**UART mode bit width (during communication at different potential) (reference)**

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)**($T_A = -40$ to $+125^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$ $4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	600		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1000		ns
SCKp high-level width	t_{KH1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 80$		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 170$		ns
SCKp low-level width	t_{KL1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 28$		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 40$		ns
Slp setup time (to SCKp \uparrow) ^{Note 1}	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	160		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	250		ns
Slp hold time (from SCKp \uparrow) ^{Note 1}	t_{SI1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	40		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	40		ns
Delay time from SCKp \downarrow to SOp output ^{Note 1}	t_{KSO1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		160	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		250	ns
Slp setup time (to SCKp \downarrow) ^{Note 2}	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	80		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	80		ns
Slp hold time (from SCKp \downarrow) ^{Note 2}	t_{SI1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	40		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	40		ns
Delay time from SCKp \uparrow to SOp output ^{Note 2}	t_{KSO1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		80	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		80	ns

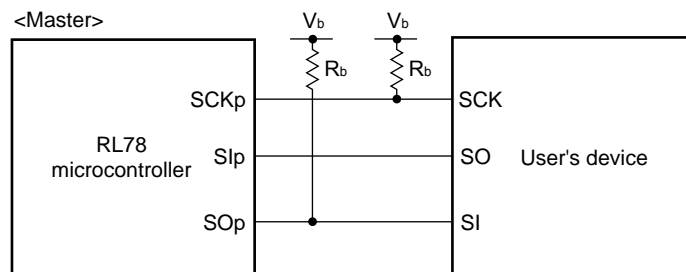
Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- Remarks**
1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[\text{F}]$: Communication line (SCKp, SOp) load capacitance, $V_b[\text{V}]$: Communication line voltage
 2. p: CSI number ($p = 00$), m: Unit number ($m = 0$), n: Channel number ($n = 0$),
g: PIM and POM number ($g = 1$)

- (1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+125^\circ\text{C}$, $2.7\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI4 to ANI7	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.4		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.8		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2, ANI4 to ANI7		0		AV_{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+125^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.4		39	μs
Conversion time	t_{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.8		39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution				± 0.60	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution				± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				± 4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution				± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI2, ANI4 to ANI7		0		V_{DD}	V
		ANI16 to ANI19		0		V_{DD}	V
		Internal reference voltage (HS (high-speed main) mode)		V_{BGR} ^{Note 3}			V
		Temperature sensor output voltage (HS (high-speed main) mode)		V_{TMPS25} ^{Note 3}			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

3.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	2.7 V ≤ V _{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	C _{erwr}	Retained for 20 years, T _A = 85°C ^{Note 3, 4}	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year, T _A = 25°C ^{Note 3, 4}		1,000,000		
		Retained for 5 years, T _A = 85°C ^{Note 3, 4}	100,000			
		Retained for 20 years, T _A = 85°C ^{Note 3, 4}	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. These are the average temperature of during the retainment.

3.9 Dedicated Flash Memory Programmer Communication (UART)

($T_A = -40$ to $+105^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps